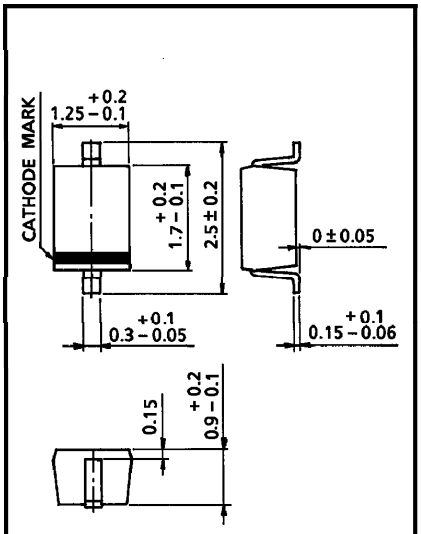
TOSHIBA DIODE SILICON EPITAXIAL PIN TYPE

JDP2S01U

UHF~VHF BAND RF ATTENUATOR APPLICATIONS

Unit in mm

- Suitable for reducing set's size as a result from enabling high-density mounting due to 2-pin small packages.
- Low Series Resistance : $r_s = 0.65\ \Omega$ (Typ.)
- Low Capacitance : $C_T = 0.7$ pF (Typ.)



USC	
JEDEC	—
EIAJ	—
TOSHIBA	1-1E1A

Weight : 0.004 g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	30	V
Foward Current	I_F	50	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	$I_R = 10\ \mu A$	30	—	—	V
Reverse Current	I_R	$V_R = 30$ V	—	—	0.1	μA
Forward Voltage	V_F	$I_F = 50$ mA	—	0.9	0.95	V
Capacitance	C_T	$V_R = 1$ V, f = 1 MHz	—	0.7	0.9	pF
Series Resistance	r_s	$I_F = 10$ mA, f = 100 MHz	—	0.65	1.0	Ω

* Signal level when capacitance is measured : Vsig = 20 mV_{rms}

MARKING

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